

Quarterly Reliability Monitoring Results

Quarters: Q1/2021 to Q4/2021

Based on structural similarity

Supplier Nexperia B.V. Name of Laboratory Assembly reliability labs Based on AEC-Q101 Test		User Part Number						
		PBSS302PX						
		Part Description						
		Nexperia DHAM Small Signal Bipolar Transistor						
		SMD package						
		Test Conditions	Duration	# Lots	# Quantity	# Rejects		
	TEST							
	Pre- and Post-Stress							
# E1	Electrical Test	Tamb = 25 °C	N/A	see below	all parts	see below		
		JESD22-A113 Bake Tamb = 125 °C	24 hours					
	PC	Soak Tamb = 85 °C, RH = 85%	168 hours					
# A1	Preconditioning	Reflow soldering	3 cycles	849	61170	0		
		MIL-STD-750-1						
	HTRB	M1039 Method A						
	High Temperature Reverse	Tj = Tjmax, Vr = 100% of max. datasheet						
[±] B1	Bias	reverse voltage	1000 hours	202	16160	0		
	тс	JESD22-A104						
# A4	Temperature Cycling	-65 °C to Tjmax, not to exceed 150°C	1000 cycles	171	13680	0		
		JESD22-A102						
	AC	Tamb = 121 °C, RH = 100 %						
# A3 alt	Autoclave	Pressure = 205 kPa (29.7 psia)	96 hours	173	13840	0		
	H3TRB	JESD22-A101 Tamb = 85 °C, RH = 85%, VR = 80 % of						
	High Humidity High Temperature Reverse Bias	rated reverse voltage ^[1]		. ===		_		
# A2 alt	Temperature Reverse Bias		1000 hours	173	13840	0		
	IOL	MIL-STD-750 Method 1037						
	IOL Intermittent Operating Life	ton = toff, devices powered to insure ΔTj =	1000	107	15760	0		
÷ A5	Intermittent Operating Life	100 C for 13000 cycles	1000 hours	197	15760	0		
	RSH	IESD22-A111						
£ C8	Resistance to Solder Heat	260 °C ± 5 °C	10 s	135	4050	0		
- C0	SD		10.5	133	4030	U		
	Solderability	J-STD-002		342	3420	0		

^[1] The maximum applied voltage is limited by test chamber set up and does not exceed 115V.

Calculation of FIT and MTTF

Test considered for FIT calculation: High Temperature Reverse Bias (HTRB, Test #B1)
Confidence level 60%, derated to 55 °C, activation energy 0.7 eV, test time 168 to 1000 hours

Wafer Fab	Technology	Quantity	Rejects	Failure Rate (FIT)	MTTF (hrs)
Nexperia	Small Signal Bipolar				
DHAM	Transistor	16160	0	0.26	3.81E+09

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